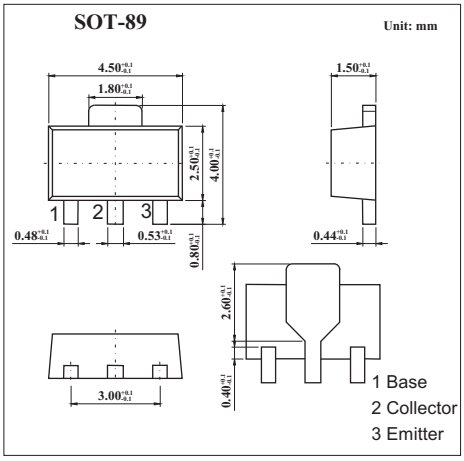
TY Semicondutor®

Product specification

KTA1663

■ Features

- Collector Power Dissipation: P_C=500mW
- Collector Current:I_C=-1.5A



■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-30	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-1.5	A
Base Current	I_B	-0.3	A
Collector Power Dissipation	P_C	500	mW
	P_C*	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	℃

* mounted on ceramic substrate (250mm^2 X 0.8t)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-1mA, I_E=0	-30			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-30			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C=0	-5.0			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-30V, I_E=0			-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0			-100	nA
DC Current Gain	h_{FE}	V_{CE}=-2V, I_C=-500mA	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-1.5A, I_B=-0.03A			-2.0	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-2V, I_C=-500mA			-1.0	V
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz			50	pF
Transition Frequency	f_T	V_{CE}=-2V, I_C=-500mA		120		MHz

■ h_{FE} Classification

Marking	HO	HY
Rank	O	Y
Range	100～200	160～320